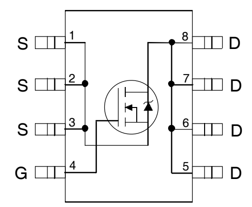
International
IOR Rectifier

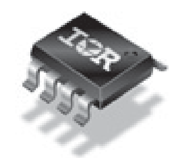
IRF8721PbF-1

HEXFET® Power MOSFET

V_{DS}	30	V
$R_{DS(on)\ max}$ (@V_{GS} = 10V)	8.5	mΩ
$Q_{g\ (typical)}$	8.3	nC
I_D (@T_A = 25°C)	14	A



Top View


SO-8

Applications

- Control MOSFET of Sync-Buck Converters used for Notebook Processor Power
- Control MOSFET for Isolated DC-DC Converters in Networking Systems

Features		Benefits
Industry-standard pinout SO-8 Package	⇒	Multi-Vendor Compatibility
Compatible with Existing Surface Mount Techniques		Easier Manufacturing
RoHS Compliant, Halogen-Free		Environmentally Friendlier
MSL1, Industrial qualification		Increased Reliability

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRF8721PbF-1	SO-8	Tube/Bulk	95	IRF8721PbF-1
		Tape and Reel	4000	IRF8721TRPbF-1

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	± 20	
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 10V	14	A
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ 10V	11	
I_{DM}	Pulsed Drain Current ①	110	
P_D @T_A = 25°C	Power Dissipation	2.5	W
P_D @T_A = 70°C	Power Dissipation	1.6	
	Linear Derating Factor	0.02	W/°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead ⑤	——	20	°C/W
$R_{\theta JA}$	Junction-to-Ambient ④⑤	——	50	

Notes ① through ⑤ are on page 9

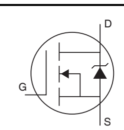
Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	V_{GS} = 0V, I_D = 250μA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.021	—	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	6.9	8.5	mΩ	V_{GS} = 10V, I_D = 14A ③
		—	10.6	12.5		V_{GS} = 4.5V, I_D = 11A ③
$V_{GS(th)}$	Gate Threshold Voltage	1.35	—	2.35	V	V_{DS} = V_{GS}, I_D = 25μA
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-6.2	—	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	V_{DS} = 24V, V_{GS} = 0V
		—	—	150		V_{DS} = 24V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V_{GS} = -20V
gfs	Forward Transconductance	27	—	—	S	V_{DS} = 15V, I_D = 11A
Q_g	Total Gate Charge	—	8.3	12	nC	
Q_{gs1}	Pre-Vth Gate-to-Source Charge	—	2.0	—		V_{DS} = 15V
Q_{gs2}	Post-Vth Gate-to-Source Charge	—	1.0	—		V_{GS} = 4.5V
Q_{gd}	Gate-to-Drain Charge	—	3.2	—		I_D = 11A
Q_{godr}	Gate Charge Overdrive	—	2.0	—		See Fig. 16a and 16b
Q_{sw}	Switch Charge (Q_{gs2} + Q_{gd})	—	4.2	—		
Q_{oss}	Output Charge	—	5.0	—	nC	V_{DS} = 16V, V_{GS} = 0V
R_G	Gate Resistance	—	1.8	3.0	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	8.2	—	ns	V_{DD} = 15V, V_{GS} = 4.5V
t_r	Rise Time	—	11	—		I_D = 11A
$t_{d(off)}$	Turn-Off Delay Time	—	8.1	—		R_G = 1.8Ω
t_f	Fall Time	—	7.0	—		See Fig. 15a
C_{iss}	Input Capacitance	—	1040	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	229	—		V_{DS} = 15V
C_{rss}	Reverse Transfer Capacitance	—	114	—		f = 1.0MHz

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	68	mJ
I_{AR}	Avalanche Current ①	—	11	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	3.1	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	112		
V_{SD}	Diode Forward Voltage	—	—	1.0	V	T_J = 25°C, I_S = 11A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	—	14	21	ns	T_J = 25°C, I_F = 11A, V_{DD} = 15V
Q_{rr}	Reverse Recovery Charge	—	15	23	nC	di/dt = 300A/μs ③
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

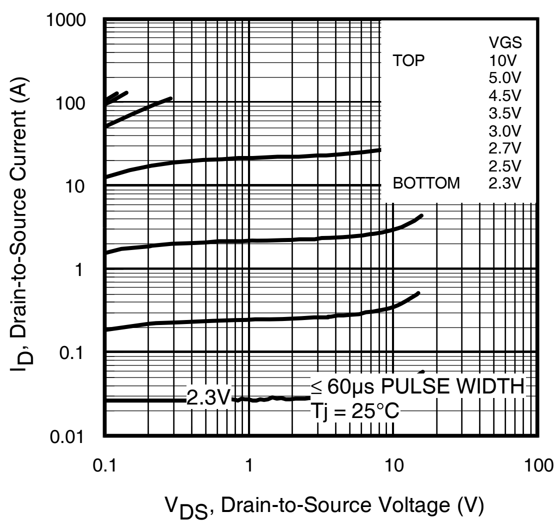


Fig 1. Typical Output Characteristics

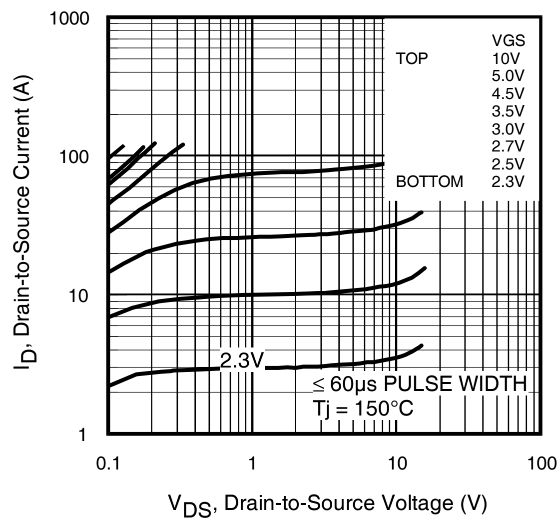


Fig 2. Typical Output Characteristics

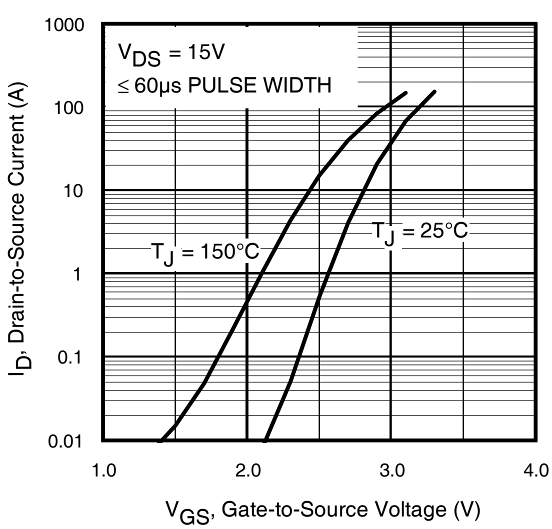


Fig 3. Typical Transfer Characteristics

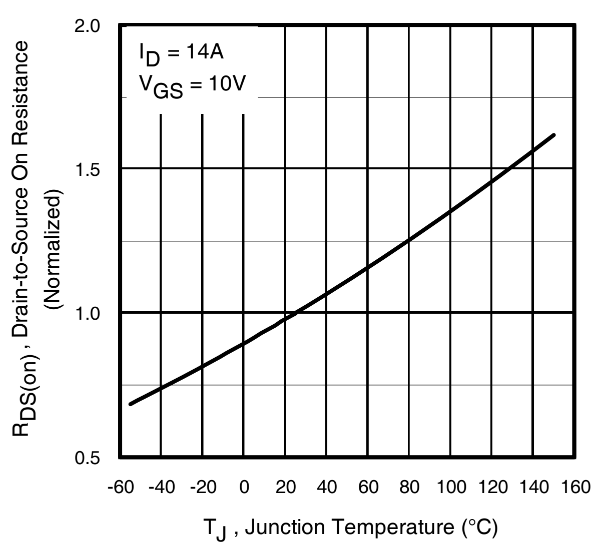


Fig 4. Normalized On-Resistance Vs. Temperature

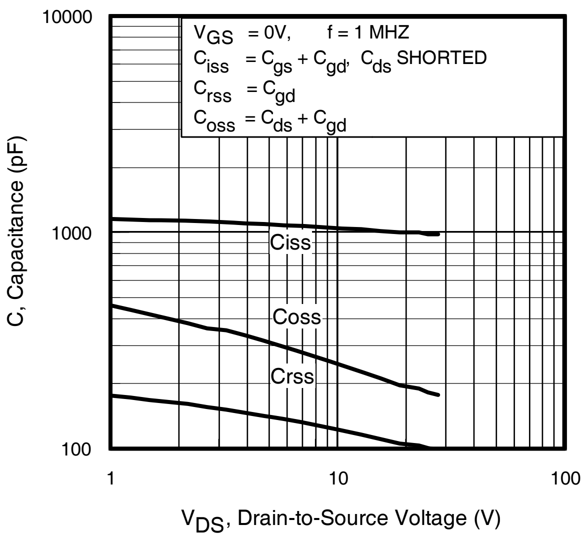


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

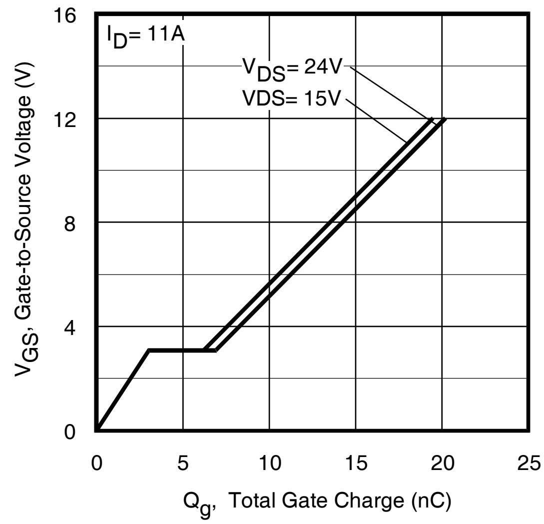


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

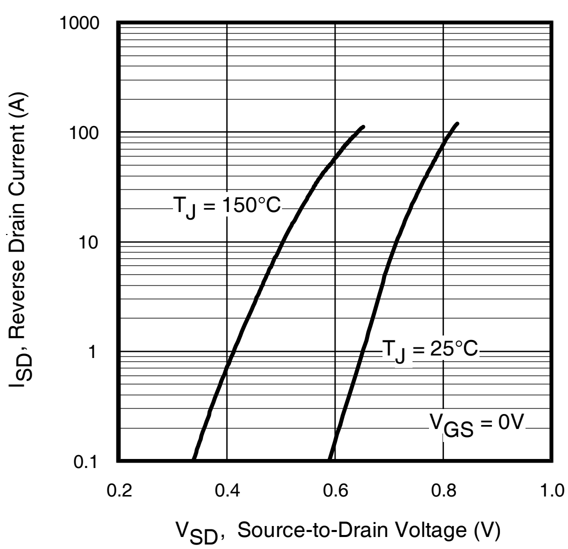


Fig 7. Typical Source-Drain Diode Forward Voltage

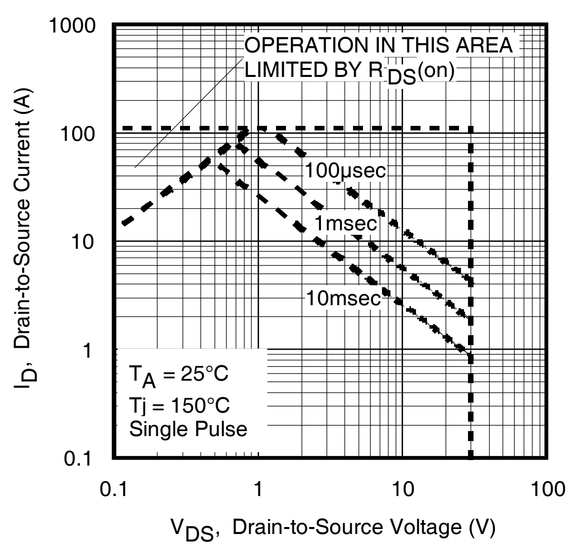


Fig 8. Maximum Safe Operating Area

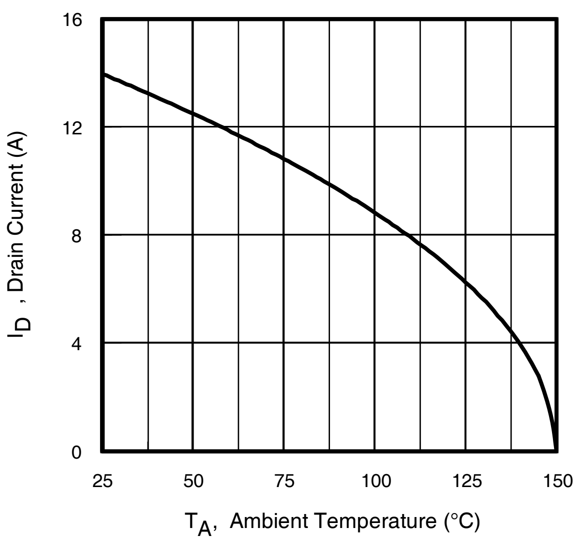


Fig 9. Maximum Drain Current Vs. Case Temperature

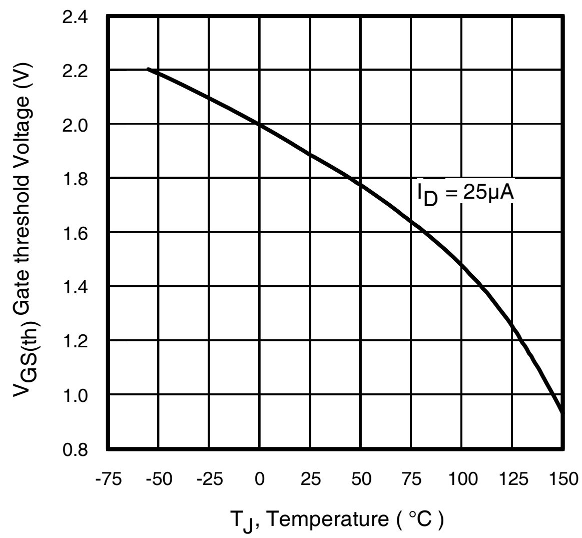
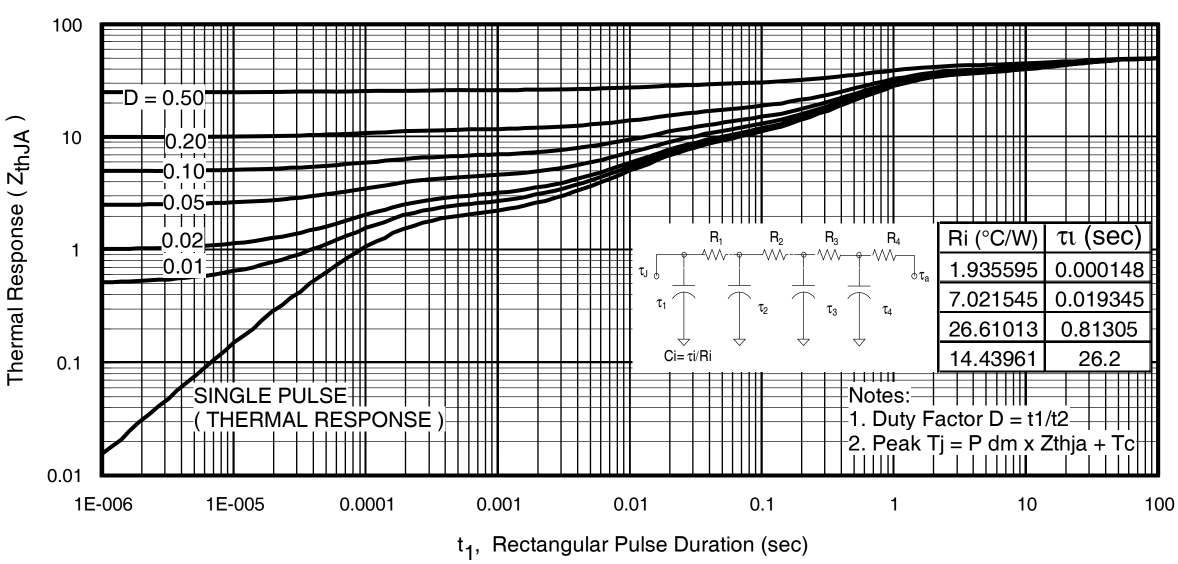


Fig 10. Threshold Voltage Vs. Temperature



Ri (°C/W)	τi (sec)
1.935595	0.000148
7.021545	0.019345
26.61013	0.81305
14.43961	26.2

Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

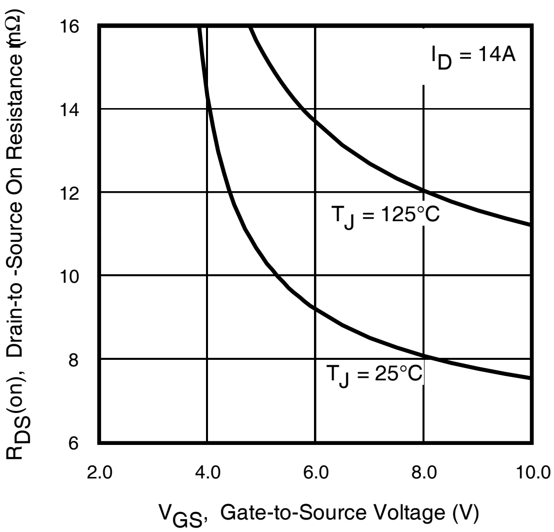


Fig 12. On-Resistance vs. Gate Voltage

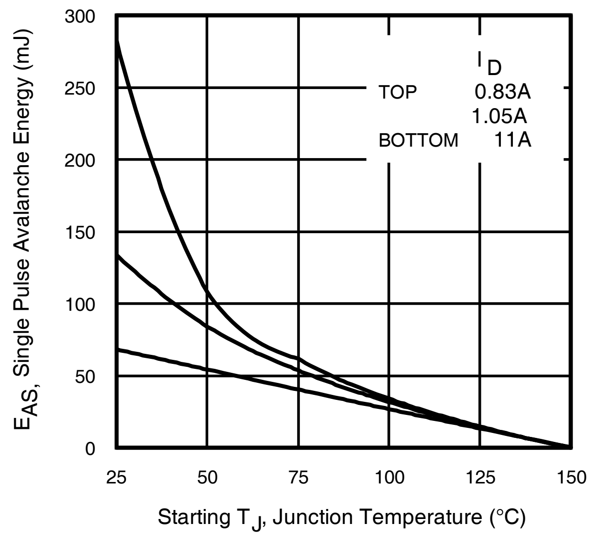


Fig 13. Maximum Avalanche Energy vs. Drain Current

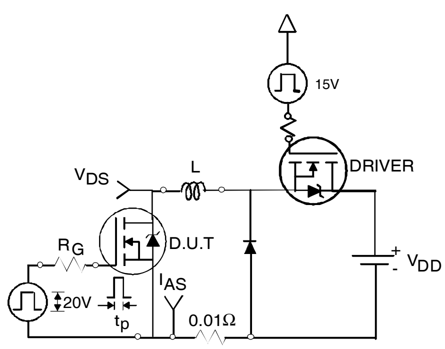


Fig 14a. Unclamped Inductive Test Circuit

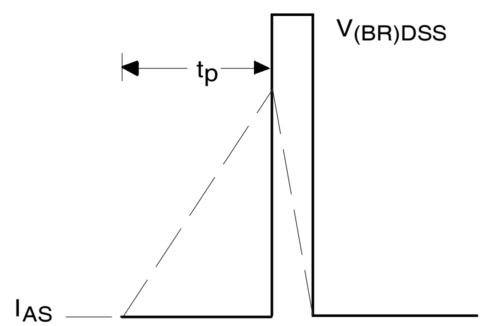


Fig 14b. Unclamped Inductive Waveforms

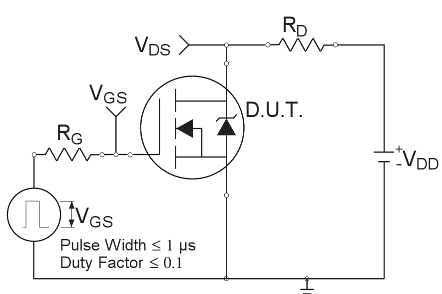


Fig 15a. Switching Time Test Circuit

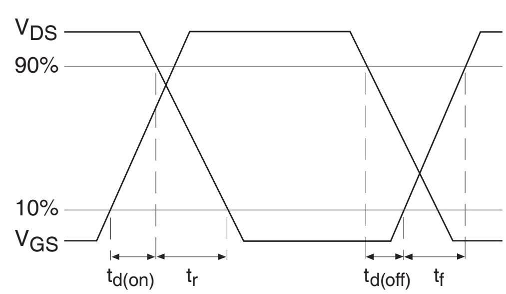


Fig 15b. Switching Time Waveforms

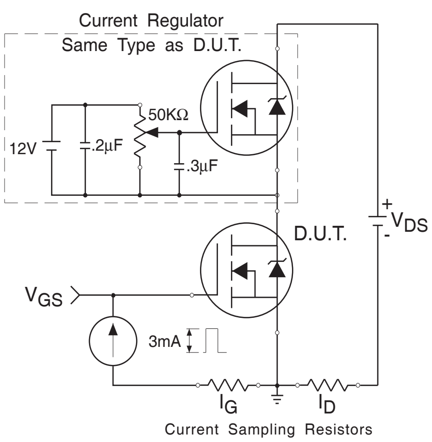


Fig 16a. Gate Charge Test Circuit

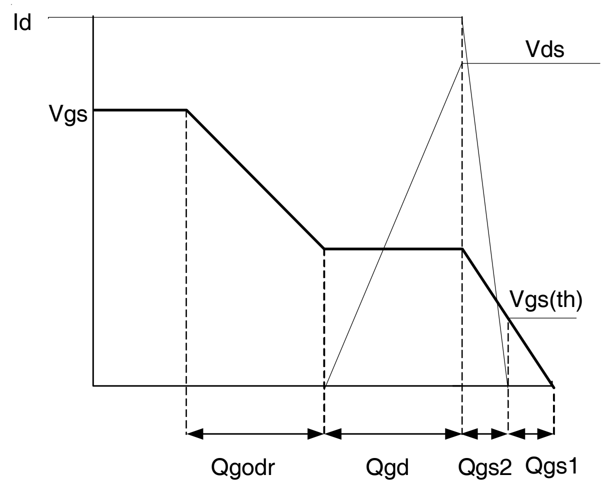
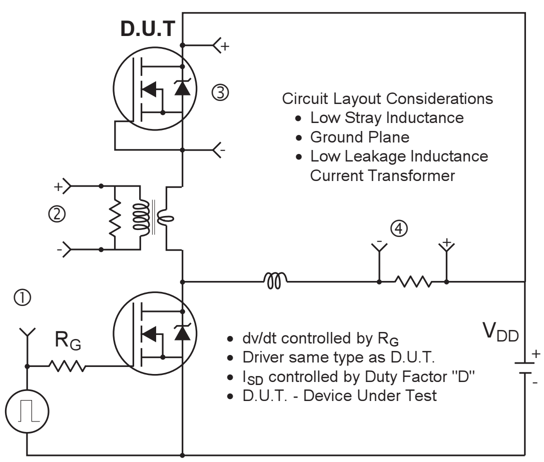
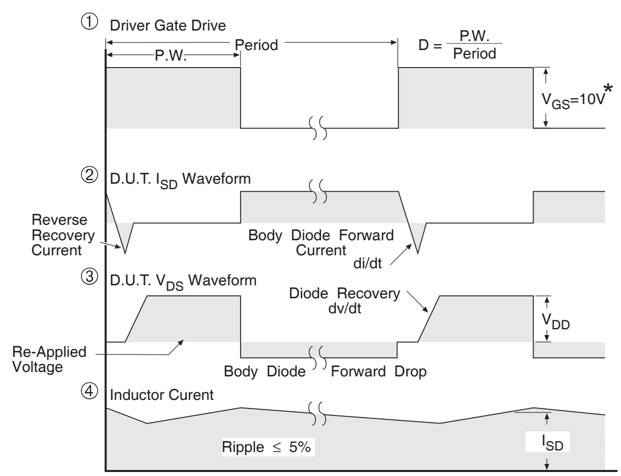


Fig 16b. Gate Charge Waveform



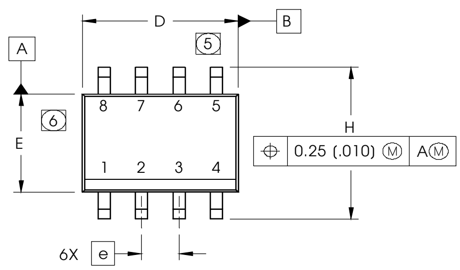


* V_{GS} = 5V for Logic Level Devices

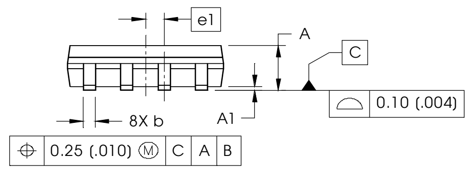
Fig 17. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

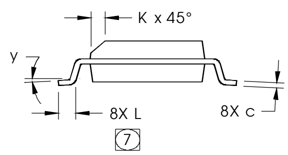
SO-8 Package Outline

Dimensions are shown in milimeters (inches)

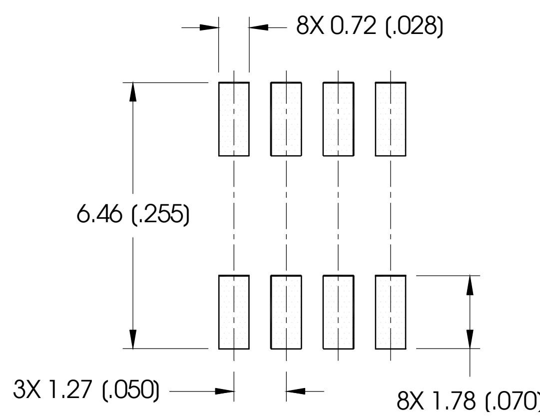


DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e 1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°





FOOTPRINT



NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.

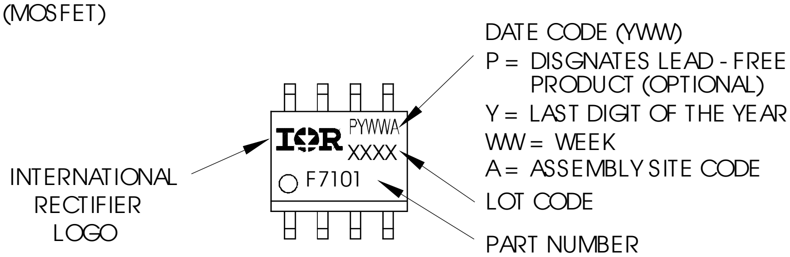
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].

6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].

7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

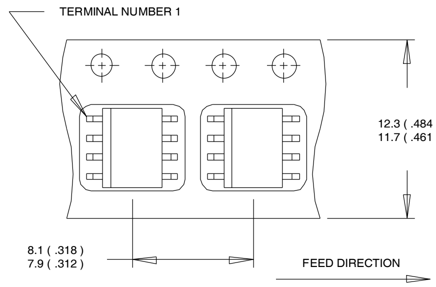
SO-8 Part Marking Information

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

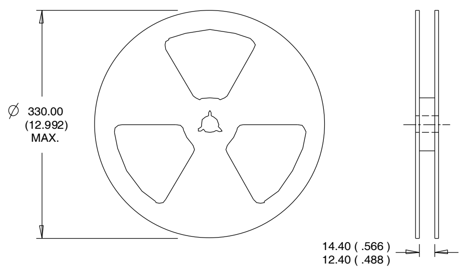


Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

SO-8 Tape and Reel (Dimensions are shown in milimeters (inches))



NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Qualification information†

Qualification level	Industrial (per JEDEC JESD47F†† guidelines)	
Moisture Sensitivity Level	SO-8	MSL1 (per JEDEC J-STD-020D††)
RoHS compliant	Yes	

† Qualification standards can be found at International Rectifier's web site: http://www.irf.com/product-info/reliability
†† Applicable version of JEDEC standard at the time of product release

Notes:
① Repetitive rating; pulse width limited by max. junction temperature.
② Starting T_J = 25°C, L = 1.09mH, R_G = 25Ω, I_{AS} = 11A.
③ Pulse width ≤ 400µs; duty cycle ≤ 2%.
④ When mounted on 1 inch square copper board.
⑤ R_θ is measured at T_J of approximately 90°C.

International Rectifier
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To contact International Rectifier, please visit http://www.irf.com/whoto-call/